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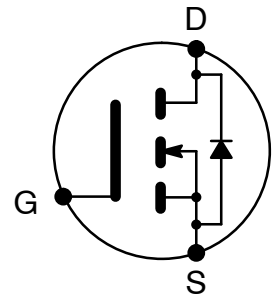
NTE2908 MOSFET N-Channel, Enhancement Mode High Speed Switch TO-220 Type Package

Description:

The NTE2908 is a Power MOSFET in a TO-220 type package that utilizes advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design provides an extremely efficient and reliable device for use in a wide variety of applications.

Features:

- Ultra Low ON-Resistance
- Dynamic dv/dt Rating
- +175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated



Absolute Maximum Ratings:

Continuous Drain Current ($V_{GS} = 10V$), I_D	
$T_C = +25^\circ C$	202A
$T_C = +100^\circ C$	143A
Pulsed Drain Current (Note 2), I_{DM}	808A
Power Dissipation ($T_C = +25^\circ C$), P_D	333W
Derate Linearly Above 25°C	2.2W/°C
Gate-to-Source Voltage, V_{GS}	±20V
Single Pulse Avalanche Energy (Note 3), E_{AS}	620mJ
Peak Diode Recovery dv/dt (Note 4), dv/dt	1.5V/ns
Operating Junction Temperature Range, T_J	-55° to +175°C
Storage Temperature Range, T_{stg}	-55° to +175°C
Lead Temperature (During Soldering, 1.6mm from case for 10sec), T_L	+300°C
Mounting Torque (6-32 or M3 Screw)	10 lbf•in (1.1N•m)
Thermal Resistance, Junction-to-Case, R_{thJC}	0.45°C/W
Thermal Resistance, Junction-to-Ambient, R_{thJA}	62°C/W
Typical Thermal Resistance, Case-to-Sink (Flat, Greased Surface), R_{thCS}	0.5°C/W

Note 1. Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 75A.

Note 2. Repetitive rating; pulse width limited by maximum junction temperature.

Note 3. Starting $T_J = +25^\circ C$, $L = 85\mu H$, $R_G = 25\Omega$, $I_{AS} = 121A$

Note 4. $I_{SD} \leq 121A$, $di/dt \leq 130A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq +175^\circ C$



Electrical Characteristics: ($T_J = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	40	-	-	V
Breakdown Voltage Temp. Coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_J}$	Reference to $+25^\circ\text{C}$, $I_D = 1\text{mA}$	-	0.039	-	$V/^\circ\text{C}$
Static Drain-to-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 121A$, Note 5	-	0.0035	0.004	Ω
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = 10V, I_D = 250\mu A$	2.0	-	4.0	V
Forward Transconductance	g_{fs}	$V_{DS} = 25V, I_D = 121A$	76	-	-	S
Drain-to-Source Leakage Current	I_{DSS}	$V_{DS} = 40V, V_{GS} = 0V$	-	-	20	μA
		$V_{DS} = 32V, V_{GS} = 0V, T_J = +150^\circ\text{C}$	-	-	250	μA
Gate-to-Source Forward Leakage	I_{GSS}	$V_{GS} = 20V$	-	-	200	nA
Gate-to-Source Reverse Leakage	I_{GSS}	$V_{GS} = -20V$	-	-	-200	nA
Total Gate Charge	Q_g	$I_D = 121A, V_{DS} = 32V, V_{GS} = 10V$, Note 5	-	131	196	nC
Gate-to-Source Charge	Q_{gs}		-	36	-	nC
Gate-to-Drain ("Miller") Charge	Q_{gd}		-	37	56	nC
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 20V, I_D = 121A, R_G = 2.5\Omega$, $R_D = 0.2\Omega$, Note 5	-	17	-	ns
Rise Time	t_r		-	190	-	ns
Turn-Off Delay Time	$t_{d(off)}$		-	46	-	ns
Fall Time	t_f		-	33	-	ns
Internal Drain Inductance	L_D	Between lead, .250in. (6.0) mm from package and center of die contact	-	4.5	-	nH
Internal Source Inductance	L_S		-	7.5	-	nH
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 25V, f = 1\text{MHz}$	-	5669	-	pF
Output Capacitance	C_{oss}		-	1659	-	pF
Reverse Transfer Capacitance	C_{rss}		-	223	-	pF
Output Capacitance	C_{oss}	$V_{GS} = 0V, V_{DS} = 1.0V, f = 1\text{MHz}$	-	6205	-	pF
		$V_{GS} = 0V, V_{DS} = 32V, f = 1\text{MHz}$	-	1467	-	pF
Effective Output Capacitance	$C_{oss \text{ eff.}}$	$V_{GS} = 0V, V_{DS} = 0V \text{ to } 32V$, Note 6	-	2249	-	pF

Source-Drain Ratings and Characteristics:

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Continuous Source Current (Body Diode)	I_S	Note 1	-	-	202	A
Pulsed Source Current (Body Diode)	I_{SM}	Note 2	-	-	808	A
Diode Forward Voltage	V_{SD}	$T_J = +25^\circ\text{C}, I_S = 121A, V_{GS} = 0V$, Note 5	-	-	1.5	V
Reverse Recovery Time	t_{rr}	$T_J = +25^\circ\text{C}, I_F = 121A$, $di/dt = 100A/\mu s$, Note 5	-	78	117	ns
Reverse Recovery Charge	Q_{rr}		-	163	245	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

Note 1. Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 75A.

Note 2. Repetitive rating; pulse width limited by maximum junction temperature.

Note 5. Pulse width $\leq 100\mu s$; duty cycle $\leq 2\%$.

Note 6. $C_{oss \text{ eff.}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

